

ABSTRACT

The present disclosure relates to a blank mask and the like, and comprises a transparent substrate and a light shielding film disposed on the transparent substrate. The light shielding film comprises a transition metal and at least any one between oxygen and nitrogen. The light shielding film comprises a first light shielding layer and a second light shielding layer disposed on the first light shielding layer. The light shielding film has an Rd value of Equation 1 below which is 0.4 to 0.8.

[Equation 1]

$$Rd = \frac{er_2}{er_1}$$

In the Equation 1, the er_1 value is an etching rate of the first light shielding layer measured by etching with argon gas.

The er_2 value is an etching rate of the second light shielding layer measured by etching with argon gas.

In such a blank mask, a resolution degradation can be suppressed effectively when the light shielding film is patterned.

FIG. 1